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**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790FG**Generic Copy

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**Issue Date:** 13-Sep-2013

**TITLE:** Final PCN for wafer fab transfer from Gunma and Gifu in Japan to Niigata in Japan (Group FG).

**PROPOSED FIRST SHIP DATE:** starting on 13-Dec-2013 (the actual ship date will be different by each product, please check with the responsible Sales person).

**AFFECTED CHANGE CATEGORY(S):** Wafer Fabrication Location Change

**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**

Contact your local ON Semiconductor Sales Office or [Yasuhiro.Igarashi@onsemi.com](mailto:Yasuhiro.Igarashi@onsemi.com).

**SAMPLES:** Contact your local ON Semiconductor Sales Office or [Katsuya.Ito@onsemi.com](mailto:Katsuya.Ito@onsemi.com)

**ADDITIONAL RELIABILITY DATA:** May be available

Contact your local ON Semiconductor Sales Office or [Kazutoshi.Kitazume@onsemi.com](mailto:Kazutoshi.Kitazume@onsemi.com)

**NOTIFICATION TYPE:**

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <[quality@onsemi.com](mailto:quality@onsemi.com)>

**DESCRIPTION AND PURPOSE:**

This is a Final Process Change Notification to announce the transfer of products from Sanyo wafer fabrication site located in Gifu to Niigata.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.



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### RELIABILITY DATA SUMMARY

#### Group FG

Test:	Conditions:	Interval:	Results:
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
(This test isn't performed for diodes)			
High Temperature Reverse Bias	Ta=150/150/125degC, VDSS/VCES/VR=max	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150/150/125degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, 2.03x10 <sup>5</sup> Pa, 100%	50 hrs	Pass
High Temperature Storage	Ta=150/150/125degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Solder Test	Ta=260degC±5degC	10 s	Pass

Notice) ※1 Pre-treatment: Resistance to Soldering heat (Flow: 260degC/10s)  
 Temperature description: 150/150/125 means FET/BIP/DIODE

### ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in the electrical performance. Datasheet specifications remain unchanged.

### CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

### List of affected parts:

#### Group FG

PART_ID
1SV234-TB-E
2SA1552S-TL-E
2SA2016-TD-E
2SB1205T-E
3SK263-5-TG-E
PCP1103-P-TD-H
PCP1203-P-TD-H
SVC236-TB-E